

# SN74HCS125 Quadruple Buffer with 3-State Outputs and Schmitt-Trigger Inputs

#### 1 Features

- Wide operating voltage range: 2 V to 6 V
- Schmitt-trigger inputs allow for slow or noisy input
- Low power consumption
  - Typical I<sub>CC</sub> of 100 nA
  - Typical input leakage current of ±100 nA
- ±7.8-mA output drive at 6 V
- Extended ambient temperature range: -40°C to +125°C, T<sub>A</sub>

### 2 Applications

- Enable or disable a digital signal
- Controlling an indicator LED
- Debounce a switch
- Eliminate slow or noisy input signals

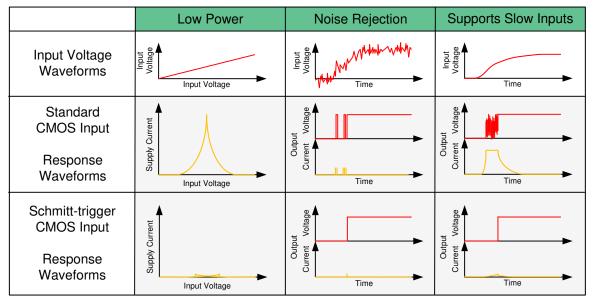
### 3 Description

The SN74HCS125 contains four independent buffers with 3-state outputs and Schmitt-trigger inputs. Each buffer performs the Boolean function Y = A in positive logic. The outputs can be put into a Hi-Z state by applying a High on the  $\overline{OE}$  pin.

#### **Device Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)
SN74HCS125PW	TSSOP (14)	5.00 mm × 4.40 mm
SN74HCS125D	SOIC (14)	9.90 mm × 3.90 mm
SN74HCS125BQA	WQFN (14)	3.00 mm × 2.50 mm

For all available packages, see the orderable addendum at the end of the data sheet.



Benefits of Schmitt-trigger inputs



### **Table of Contents**

1 Features	1	8.3 Feature Description	9
2 Applications	1	8.4 Device Functional Modes	
3 Description		9 Application and Implementation	11
4 Revision History		9.1 Application Information	11
5 Pin Configuration and Functions	3	9.2 Typical Application	
Pin Functions	3	10 Power Supply Recommendations	14
6 Specifications	4	11 Layout	14
6.1 Absolute Maximum Ratings	4	11.1 Layout Guidelines	14
6.2 ESD Ratings	4	11.2 Layout Example	
6.3 Recommended Operating Conditions	4	12 Device and Documentation Support	15
6.4 Thermal Information	<mark>5</mark>	12.1 Documentation Support	15
6.5 Electrical Characteristics	<mark>5</mark>	12.2 Receiving Notification of Documentation Updates	s15
6.6 Switching Characteristics	5	12.3 Support Resources	15
6.7 Operating Characteristics		12.4 Trademarks	15
6.8 Typical Characteristics	7	12.5 Electrostatic Discharge Caution	15
7 Parameter Measurement Information		12.6 Glossary	15
8 Detailed Description	9	13 Mechanical, Packaging, and Orderable	
8.1 Overview		Information	16
8.2 Functional Block Diagram	9		

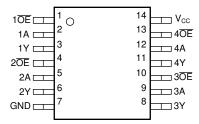
# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision (June 2020) to Revision A (January 2021)	Page
•	Updated the numbering fomat for tables, figures and cross-references throughout the document	1
•	Added BQA package information to Device Information	<mark>1</mark>
•	Added BQA package to Pin Configuration and Functions	3
•	Added BQA package information to Thermal Information table	<mark>5</mark>



# **5 Pin Configuration and Functions**



D or PW Package 14-Pin SOIC or TSSOP Top View

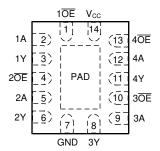


Figure 5-1. BQA Package 14-Pin WQFN Top View

#### **Pin Functions**

PIN		I/O	DESCRIPTION			
NAME	NO.	1/0	DESCRIPTION			
1 OE	1	Input	Channel 1, Output Enable, Active Low			
1A	2	Input	Channel 1, Input A			
1Y	3	Output	Channel 1, Output Y			
2 OE	4	Input	Channel 2, Output Enable, Active Low			
2A	5	Input	Channel 2, Input A			
2Y	6	Output	Channel 2, Output Y			
GND	7	_	Ground			
3Y	8	Output	Channel 3, Output Y			
3A	9	Input	Channel 3, Input A			
3 OE	10	Input	Channel 3, Output Enable, Active Low			
4Y	11	Output	Channel 4, Output Y			
4A	12	Input	Channel 4, Input A			
4 OE	13	Input	Channel 4, Output Enable, Active Low			
V <sub>CC</sub>	14	_	Positive Supply			
Thermal Pad <sup>(1)</sup>		_	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.			

### 1. BQA package only.



### **6 Specifications**

### **6.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	$V_I < 0$ or $V_I > V_{CC}$		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
Io	Continuous output current	$V_{O} = 0$ to $V_{CC}$		±35	mA
Icc	Continuous current through V <sub>CC</sub> or GND	·		±70	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

#### 6.2 ESD Ratings

			VALUE	UNIT
V	Floatroatatia diaabarga	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 <sup>(1)</sup>	±4000	V
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

#### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2	5	6	V
VI	Input voltage	0		V <sub>CC</sub>	V
Vo	Output voltage	0		V <sub>CC</sub>	V
T <sub>A</sub>	Ambient temperature	-55		125	°C

Product Folder Links: SN74HCS125



### **6.4 Thermal Information**

THERMAL METRIC <sup>(1)</sup>		PW (TSSOP)	D (SOIC	BQA (WQFN)	UNIT
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	151.7	133.6	109.7	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	79.4	89	111.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	94.7	89.5	77.9	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	25.2	45.5	20.2	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	94.1	89.1	77.8	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	56.6	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at  $T_A$  = 25°C (unless otherwise noted).

	PARAMETER	TEST CO	NDITIONS	V <sub>cc</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
				2 V	0.7		1.5	
V <sub>T+</sub>	Positive switching threshold			4.5 V	1.7		3.15	V
				6 V	2.1		4.2	
				2 V	0.3		1	
V <sub>T-</sub>	Negative switching threshold			4.5 V	0.9		2.2	V
				6 V	1.2		3	
				2 V	0.2		1	
$\Delta V_T$	Hysteresis (V <sub>T+</sub> - V <sub>T-</sub> ) <sup>(1)</sup>			4.5 V	0.4		1.4	V
				6 V	0.6		1.6	
			I <sub>OH</sub> = -20 μA	2 V to 6 V	V <sub>CC</sub> - 0.1	V <sub>CC</sub> - 0.002		
V <sub>OH</sub>	High-level output voltage	$V_I = V_{IH}$ or $V_{IL}$	I <sub>OH</sub> = -6 mA	4.5 V	4	4.3		V
			I <sub>OH</sub> = -7.8 mA	6 V	5.4	5.75		
			I <sub>OL</sub> = 20 μA	2 V to 6 V		0.002	0.1	
V <sub>OL</sub>	Low-level output voltage	$V_I = V_{IH}$ or $V_{IL}$	I <sub>OL</sub> = 6 mA	4.5 V		0.18	0.3	V
			I <sub>OL</sub> = 7.8 mA	6 V		0.22	0.33	
I <sub>I</sub>	Input leakage current	$V_I = V_{CC}$ or 0		6 V		±100	±1000	μA
l <sub>oz</sub>	Off-state (high-impedance state) output current	$V_O = V_{CC}$ or 0		6 V		0.01	2	μA
I <sub>CC</sub>	Supply current	$V_I = V_{CC}$ or 0, $I_C$	<sub>D</sub> = 0	6 V		0.1	2	μA
Ci	Input capacitance			2 V to 6 V			5	pF

<sup>(1)</sup>  $T_A = 25^{\circ}C$ 

### 6.6 Switching Characteristics

over operating free-air temperature range; typical values measured at  $T_A$  = 25°C (unless otherwise noted). See Parameter Measurement Information.

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub>	MIN	TYP	MAX	UNIT	
				2 V		12	39		
t <sub>pd</sub>	Propagation delay	A	Α	Y	4.5 V		6	26	ns
				6 V		5	24		



over operating free-air temperature range; typical values measured at  $T_A$  = 25°C (unless otherwise noted). See Parameter Measurement Information.

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub>	MIN	TYP	MAX	UNIT							
				2 V		14	24								
t <sub>en</sub>	Enable time	ŌĒ	Υ	4.5 V		7	10	ns							
				6 V		6	9								
		2 V		12	16										
t <sub>dis</sub>	Disable time	ŌĒ	ŌĒ	ŌĒ	ŌĒ	ŌĒ	ŌĒ	ŌĒ	ŌĒ	Y	4.5 V		9	10	ns
				6 V		8	9								
				2 V		9	16								
t <sub>t</sub>	Transition-time		Any	4.5 V		5	9	ns							
				6 V		4	8								

# **6.7 Operating Characteristics**

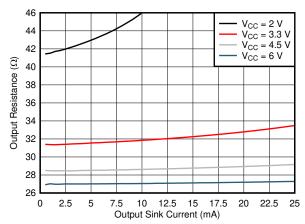
over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C <sub>pd</sub>	Power dissipation capacitance per gate	No load		10		pF

Submit Document Feedback

### **6.8 Typical Characteristics**

 $T_A = 25^{\circ}C$ 



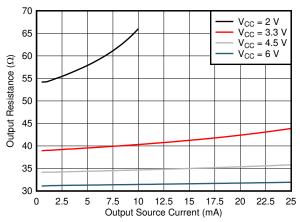
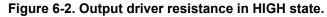
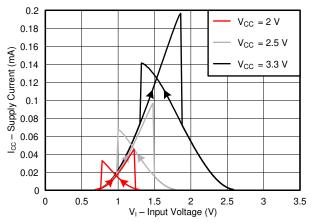


Figure 6-1. Output driver resistance in LOW state.





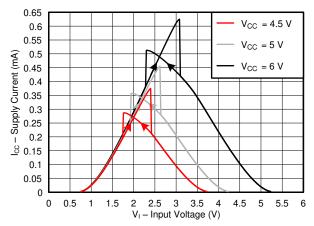


Figure 6-3. Supply current across input voltage, 2-, 2.5-, and 3.3-V supply

Figure 6-4. Supply current across input voltage, 4.5-, 5-, and 6-V supply

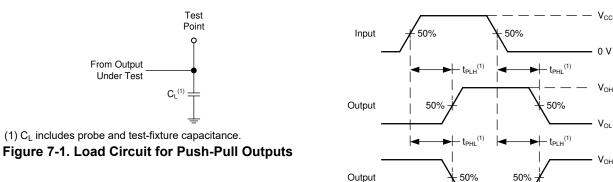


#### 7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O$  = 50  $\Omega$ ,  $t_t$  < 2.5 ns.

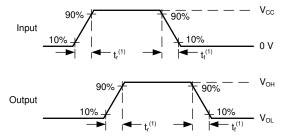
For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) The greater between  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  is the same as  $t_{\text{pd}}$ .

Figure 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t<sub>r</sub> and t<sub>f</sub> is the same as t<sub>t</sub>.

Figure 7-3. Voltage Waveforms, Input and Output Transition Times

Submit Document Feedback

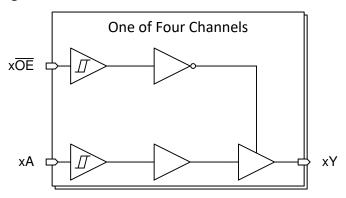
Copyright © 2021 Texas Instruments Incorporated

### 8 Detailed Description

#### 8.1 Overview

This device contains four independent buffers with 3-state outputs and Schmitt-trigger inputs. Each buffer performs the Boolean function Y = A in positive logic. The outputs can be put into a Hi-Z state by applying a High on the  $\overline{OE}$  pin.

### 8.2 Functional Block Diagram



#### 8.3 Feature Description

#### 8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

#### 8.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law  $(R = V \div I)$ .

The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

#### 8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Electrical Placement of Clamping Diodes for Each Input and Output.

#### **CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



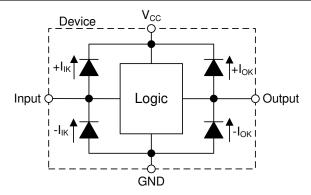


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

### 8.4 Device Functional Modes

Function Table lists the functional modes of the SN74HCS125.

**Table 8-1. Function Table** 

INPU	TS <sup>(1)</sup>	OUTPUT				
ŌĒ	Α	Υ				
L	Н	Н				
L	L	L				
Н	Х	Z				

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care

Submit Document Feedback

Copyright © 2021 Texas Instruments Incorporated



### 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

In this application, a buffer with a 3-state output is used to disable a data signal as shown in Figure 9-1. The remaining three buffers can be used for signal conditioning in other places in the system, or the inputs can be grounded and the channels left unused.

### 9.2 Typical Application

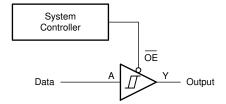


Figure 9-1. Typical application block diagram

#### 9.2.1 Design Requirements

#### 9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS125 plus the maximum static supply current,  $I_{CC}$ , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS125 plus the maximum supply current, I<sub>CC</sub>, listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS125 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCS125 can drive a load with total resistance described by  $R_L \ge V_O$  /  $I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.



#### CAUTION

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 9.2.1.2 Input Considerations

Input signals must cross  $V_{t-(min)}$  to be considered a logic LOW, and  $V_{t+(max)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS125, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74HCS125 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the  $\Delta V_{T(min)}$  in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V<sub>CC</sub> or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

#### 9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to Feature Description section for additional information regarding the outputs for this device.

#### 9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the *Layout* section.
- Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal
  performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS125
  to the receiving device(s).
- 3. Ensure the resistive load at the output is larger than (V<sub>CC</sub> / I<sub>O(max)</sub>) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.



### 9.2.3 Application Curves

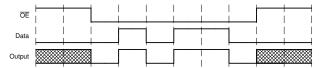


Figure 9-2. Application timing diagram

### 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

#### 11 Layout

#### 11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V<sub>CC</sub>, whichever makes more sense for the logic function or is more convenient.

#### 11.2 Layout Example

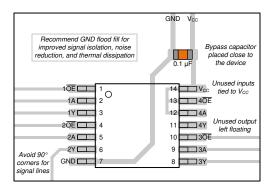


Figure 11-1. Example layout for the SN74HCS125



### 12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### **12.1 Documentation Support**

#### 12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, HCMOS Design Considerations application report (SCLA007)
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report (SDYA009)
- Texas Instruments, Designing With Logic application report

#### 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 12.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 12.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 12.6 Glossary

**TI Glossary** 

This glossary lists and explains terms, acronyms, and definitions.



# 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



### PACKAGE OPTION ADDENDUM

3-Feb-2021

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74HCS125BQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS125	Samples
SN74HCS125DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	HCS125	Samples
SN74HCS125PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	HCS125	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.



# **PACKAGE OPTION ADDENDUM**

3-Feb-2021

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74HCS125:

Automotive: SN74HCS125-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

# PACKAGE MATERIALS INFORMATION

www.ti.com 17-Apr-2021

### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS125BQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
SN74HCS125DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HCS125DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCS125PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

www.ti.com 17-Apr-2021



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS125BQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
SN74HCS125DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HCS125DR	SOIC	D	14	2500	853.0	449.0	35.0
SN74HCS125PWR	TSSOP	PW	14	2000	853.0	449.0	35.0

# D (R-PDSO-G14)

### PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



# D (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

### PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
  - Sody length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



# PW (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PLASTIC QUAD FLAT PACK-NO LEAD



- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

### **IMPORTANT NOTICE AND DISCLAIMER**

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (https://www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2021, Texas Instruments Incorporated